HEF4093B-Q100

Quad 2-input NAND Schmitt trigger

Rev. 1 — 12 July 2012 **Product data sheet**

1. General description

The HEF4093B-Q100 is a quad two-input NAND gate. Each input has a Schmitt trigger circuit. The gate switches at different points for positive-going and negative-going signals. The difference between the positive voltage (V_{T+}) and the negative voltage (V_{T-}) is defined as hysteresis voltage (V_H).

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD}, V_{SS}, or another input.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Schmitt trigger input discrimination
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- ESD protection:
  - MIL-STD-833, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pf, R = 0 Ω)
- Complies with JEDEC standard JESD 13-B

3. Applications

- Wave and pulse shapers
- Astable multivibrators
- Monostable multivibrators

4. Ordering information

Table 1. Ordering information

All types operate from –40 °C to +125 °C

Type number	Package		
	Name	Description	Version
HEF4093BT-Q100	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1

5. Functional diagram

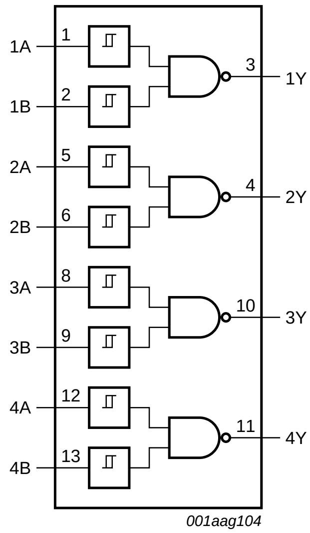


Fig 1. Functional diagram

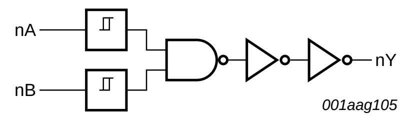


Fig 2. Logic diagram (one gate)

6. Pinning information

6.1 Pinning

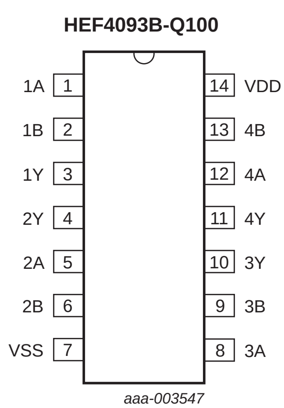


Fig 3. Pin configuration

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A to 4A	1, 5, 8, 12	input
1B to 4B	2, 6, 9, 13	input
1Y to 4Y	3, 4, 10, 11	output
V_{DD}	14	supply voltage
V_{SS}	7	ground (0 V)

7. Functional description

Table 3. Function table[1]

Input		Output
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to V_{SS} = 0 V (ground).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DD}	supply voltage			–0.5	+18	V
I_{IK}	input clamping current	V_I < –0.5 V or V_I > V_{DD} + 0.5 V		-	±10	mA
V_I	input voltage			–0.5	V_{DD} + 0.5	V
I_{OK}	output clamping current	V_O < –0.5 V or V_O > V_{DD} + 0.5 V		-	±10	mA
$I_{I/O}$	input/output current			-	±10	mA
I_{DD}	supply current			-	50	mA
T_{stg}	storage temperature			–65	+150	°C
T_{amb}	ambient temperature			–40	+125	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C				
		SO14	[1]	-	500	mW
P	power dissipation	per output		-	100	mW

[1] For SO14 package: above T_{amb} = 70 °C, P_{tot} derates linearly with 8 mW/K.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		3	15	V
V_I	input voltage		0	V_{DD}	V
T_{amb}	ambient temperature	in free air	–40	+125	°C

10. Static characteristics

Table 6. Static characteristics

V_{SS} = 0 V; V_I = V_{SS} or V_{DD}; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T_{amb} = –40 °C		T_{amb} = +25 °C		T_{amb} = +85 °C		T_{amb} = +125 °C		Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
V_{OH}	HIGH-level output voltage	$\|I_O\|$ < 1 μA	5 V	4.95	-	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level output voltage	$\|I_O\|$ < 1 μA	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V
I_{OH}	HIGH-level output current	V_O = 2.5 V	5 V	–1.7	-	–1.4	-	–1.1	-	–1.1	-	mA
		V_O = 4.6 V	5 V	–0.64	-	–0.5	-	–0.36	-	–0.36	-	mA
		V_O = 9.5 V	10 V	–1.6	-	–1.3	-	–0.9	-	–0.9	-	mA
		V_O = 13.5 V	15 V	–4.2	-	–3.4	-	–2.4	-	–2.4	-	mA
I_{OL}	LOW-level output current	V_O = 0.4 V	5 V	0.64	-	0.5	-	0.36	-	0.36	-	mA
		V_O = 0.5 V	10 V	1.6	-	1.3	-	0.9	-	0.9	-	mA
		V_O = 1.5 V	15 V	4.2	-	3.4	-	2.4	-	2.4	-	mA
I_I	input leakage current		15 V	-	±0.1	-	±0.1	-	±1.0	-	±1.0	μA
I_{DD}	supply current	all valid input combinations; I_O = 0 A	5 V	-	0.25	-	0.25	-	7.5	-	7.5	μA
			10 V	-	0.5	-	0.5	-	15.0	-	15.0	μA
			15 V	-	1.0	-	1.0	-	30.0	-	30.0	μA
C_I	input capacitance			-	-	-	7.5	-	-	-	-	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics

T_{amb} = 25 °C; C_L = 50 pF; $t_r = t_f \leq 20$ ns; wave forms see Figure 4; test circuit see Figure 5; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula[1]	Min	Typ	Max	Unit
t_{PHL}	HIGH to LOW propagation delay	nA or nB to nY	5 V	63 ns + (0.55 ns/pF)C_L	-	90	185	ns
			10 V	29 ns + (0.23 ns/pF)C_L	-	40	80	ns
			15 V	22 ns + (0.16 ns/pF)C_L	-	30	60	ns
t_{PLH}	LOW to HIGH propagation delay	nA or nB to nY	5 V	58 ns + (0.55 ns/pF)C_L	-	85	170	ns
			10 V	29 ns + (0.23 ns/pF)C_L	-	40	80	ns
			15 V	22 ns + (0.16 ns/pF)C_L	-	30	60	ns
t_{THL}	HIGH to LOW output transition time	nY to LOW	5 V	10 ns + (1.00 ns/pF)C_L	-	60	120	ns
			10 V	9 ns + (0.42 ns/pF)C_L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C_L	-	20	40	ns
t_{TLH}	LOW to HIGH output transition time	nA or nB to HIGH	5 V	10 ns + (1.00 ns/pF)C_L	-	60	120	ns
			10 V	9 ns + (0.42 ns/pF)C_L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C_L	-	20	40	ns

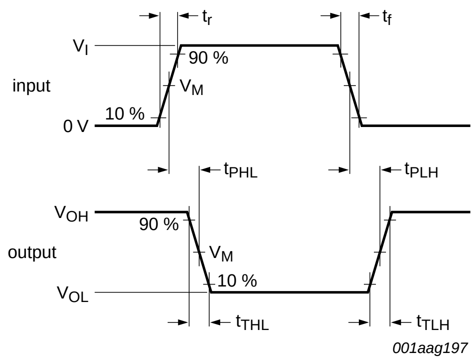
[1] Typical value of the propagation delay and output transition time can be calculated with the extrapolation formula (C_L in pF).

Table 8. Dynamic power dissipation

V_{SS} = 0 V; $t_r = t_f \leq 20$ ns; T_{amb} = 25 °C.

Symbol	Parameter	V_{DD}	Typical formula	where:
P_D	dynamic power dissipation	5 V	$P_D = 1300 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ (μW)	f_i = input frequency in MHz;
		10 V	$P_D = 6400 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ (μW)	f_o = output frequency in MHz;
		15 V	$P_D = 18700 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ (μW)	C_L = output load capacitance in pF;
				$\Sigma(f_o \times C_L)$ = sum of the outputs;
				V_{DD} = supply voltage in V.

12. Waveforms



Measurement points are given in Table 9.

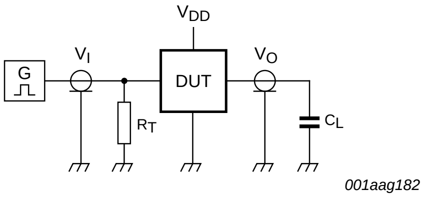
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

t_r, t_f = input rise and fall times.

Fig 4. Propagation delay and output transition time

Table 9. Measurement points

Supply voltage	Input	Output
V_{DD}	V_M	V_M
5 V to 15 V	$0.5V_{DD}$	$0.5V_{DD}$



Test data given in Table 10.

Definitions for test circuit:

DUT = Device Under Test.

C_L = load capacitance including jig and probe capacitance.

R_T = termination resistance should be equal to the output impedance Z_o of the pulse generator.

Fig 5. Test circuit

Table 10. Test data

Supply voltage	Input		Load
V_{DD}	V_I	t_r, t_f	C_L
5 V to 15 V	V_{SS} or V_{DD}	≤ 20 ns	50 pF

13. Transfer characteristics

Table 11. Transfer characteristics

V_{SS} = 0 V; T_{amb} = 25 °C; see Figure 6 and Figure 7.

Symbol	Parameter	Conditions	V_{DD}	Min	Typ	Max	Unit
V_{T+}	positive-going threshold voltage		5 V	1.9	2.9	3.5	V
			10 V	3.6	5.2	7	V
			15 V	4.7	7.3	11	V
V_{T-}	negative-going threshold voltage		5 V	1.5	2.2	3.1	V
			10 V	3	4.2	6.4	V
			15 V	4	6.0	10.3	V
V_H	hysteresis voltage		5 V	0.4	0.7	-	V
			10 V	0.6	1.0	-	V
			15 V	0.7	1.3	-	V

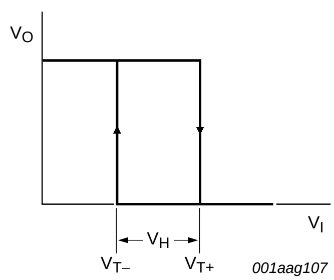


Fig 6. Transfer characteristic

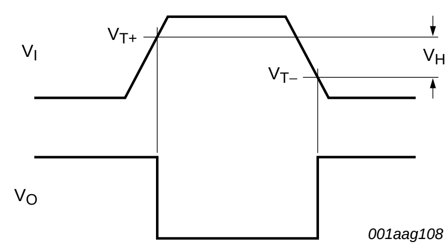
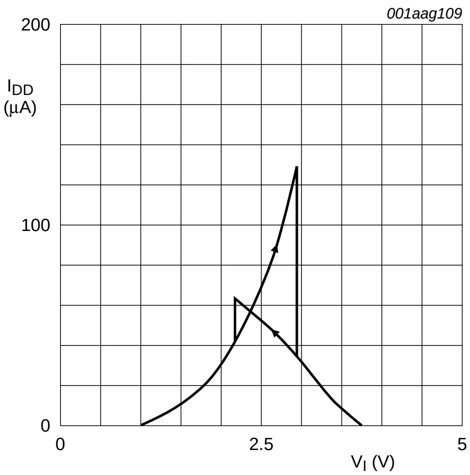
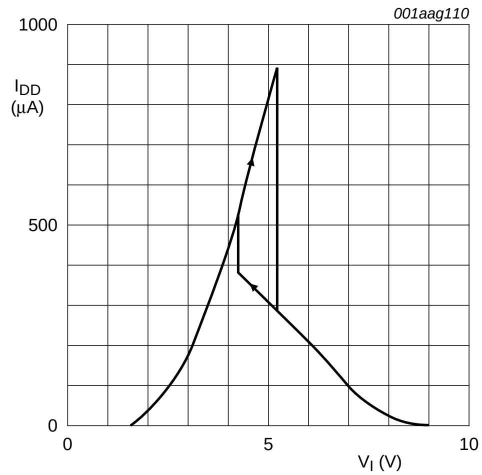


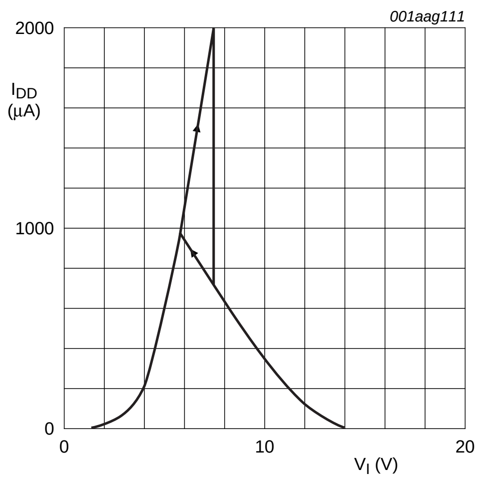
Fig 7. Waveforms showing definition of V_{T+} and V_{T-} (between limits at 30 % and 70 %) and V_H



a. V_{DD} = 5 V; T_{amb} = 25 °C

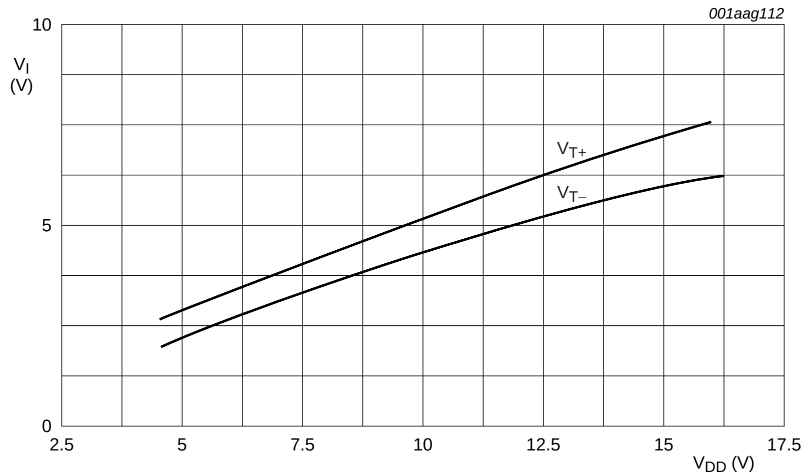


b. V_{DD} = 10 V; T_{amb} = 25 °C



c. V_{DD} = 15 V; T_{amb} = 25 °C

Fig 8. Typical drain current as a function of input



T_{amb} = 25 °C.

Fig 9. Typical switching levels as a function of supply voltage

14. Application information

Some examples of applications for the HEF4093B-Q100 are:

- Wave and pulse shapers
- Astable multivibrators
- Monostable multivibrators

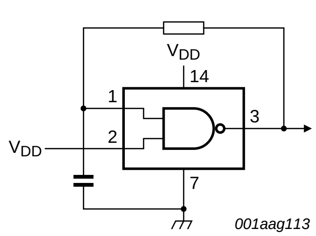


Fig 10. Astable multivibrator

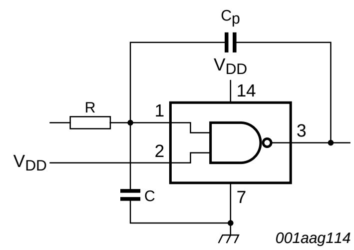


Fig 11. Schmitt trigger driven via a high-impedance input

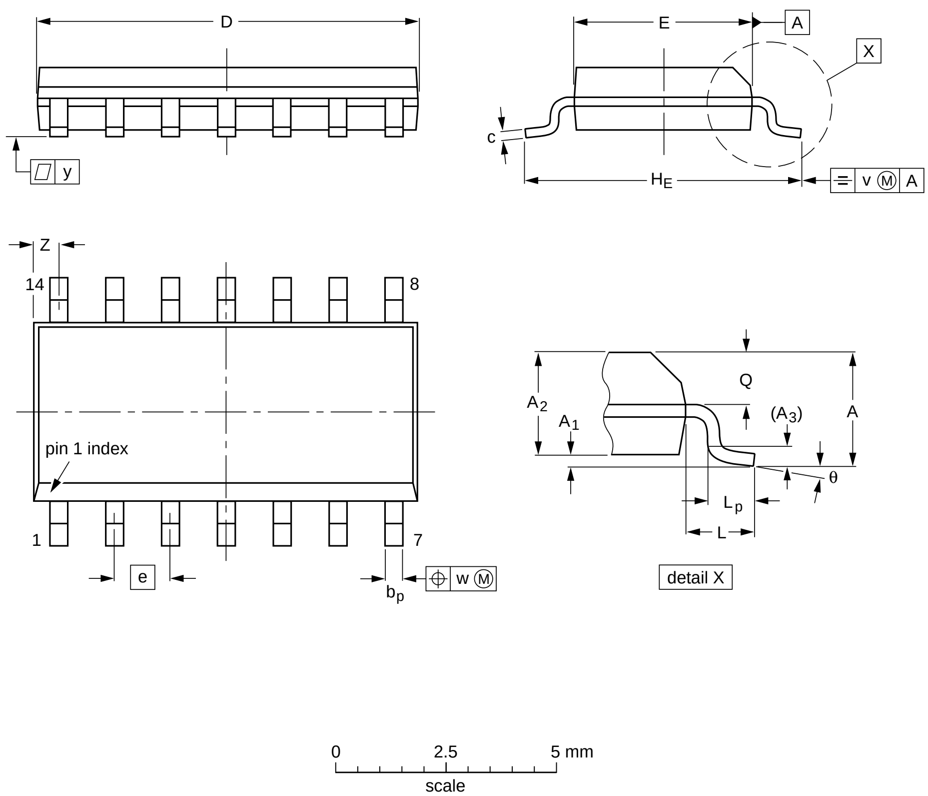
If a Schmitt trigger is driven via a high-impedance (R > 1 kΩ), then it is necessary to incorporate a capacitor C with a value of $\frac{C}{C_P} > \frac{V_{DD} - V_{SS}}{V_H}$; otherwise oscillation can occur on the edges of a pulse.

C_p is the external parasitic capacitance between inputs and output; the value depends on the circuit board layout.

Remark: The two inputs may be connected together, but this will result in a larger through-current at the moment of switching.

15. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm **SOT108-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D(1)	E(1)	e	H_E	L	L_p	Q	v	w	y	Z(1)	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT108-1	076E06	MS-012				~~99-12-27~~ 03-02-19

Fig 12. Package outline SOT108-1 (SO14)

16. Abbreviations

Table 12. Abbreviations

Acronym	Description
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
MIL	Military

17. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4093B_Q100 v.1	20120712	Product specification	-	-

18. Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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20. Contents

Date of release: 12 July 2012

Document identifier: HEF4093B_Q100